

ABSTRACT OF THE DISCLOSURE

There is provided a film-forming surface reforming method that comprises the steps of bringing a gas or an aqueous solution containing ammonia, hydrazine, amine, amino compound or their derivative into contact with a film-forming surface before an insulating film is formed on the film-forming surface of a substrate, and bringing a gas or an aqueous solution containing hydrogen peroxide, ozone, oxygen, nitric acid, sulfuric acid or their derivative into contact with the film-forming surface.